

N-Channel MOSFET, 1.1 A, 250 V Depletion, 8-Pin DFN Microchip

Manufacturers	<a href="#">Microchip Technology, Inc</a>
Package/Case	DFN5x5-8
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for DN2625DK6-G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

DN2625 is a low threshold depletion-mode (normally-on) transistor utilizing an advanced vertical DMOS structure and well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown. Vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired. The DN2625DK6-G contains two MOSFETs in an 8-lead, dual pad DFN package. The DN2625K6-G in the 14-lead QFN package is not recommended for new designs, but may continue to be purchased for existing designs.

## Features

Very low gate threshold voltage

Designed to be source-driven

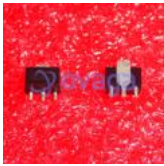
Low switching losses

Low effective output capacitance

Designed for inductive loads

Well matched for low second harmonic when driven by MD2130

## Related Products



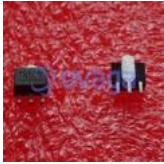
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